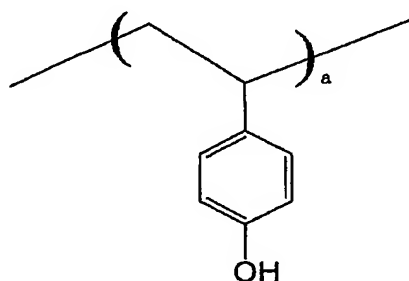


**WHAT IS CLAIMED IS:**

1. An organic anti-reflective composition comprising a crosslinking agent, a light absorbing agent, a thermal acid generator, an organic solvent and an adhesivity enhancer represented by the following Chemical Formula 1:

5                      Chemical Formula 1



wherein

a is the degree of polymerization, ranging from 30 to 400.

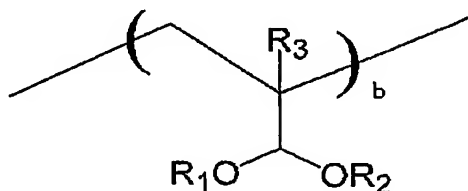
2. The organic anti-reflective composition according to Claim 1, which comprises:

- 10                      (a) 100 parts by weight of crosslinking agent;
- (b) 30 to 400 parts by weight of light absorbing agent;
- (c) 10 to 200 parts by weight thermal acid generator;
- (d) 30 to 400 parts by weight of adhesivity enhancer represented by Chemical
- Formula 1; and
- 15                      (e) 1,000 to 10,000 parts by weight of organic solvent.

3. The organic anti-reflective composition according to Claim 2, wherein said

crosslinking agent is the compound represented by the following Chemical Formula 2:

Chemical Formula 2



wherein

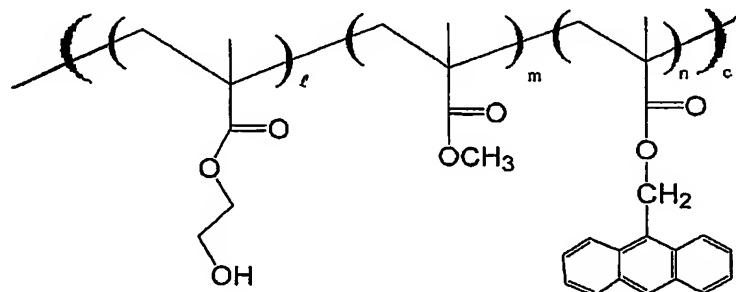
5            b is the degree of polymerization, ranging from 10 to 100;

each of  $\text{R}_1$  and  $\text{R}_2$  is  $\text{C}_1$  to  $\text{C}_4$  alkyl; and

$\text{R}_3$  is hydrogen or methyl.

4. The organic anti-reflective composition according to Claim 2, wherein said light absorbing agent is the compound represented by the following Chemical Formula 3:

10            Chemical Formula 3



wherein

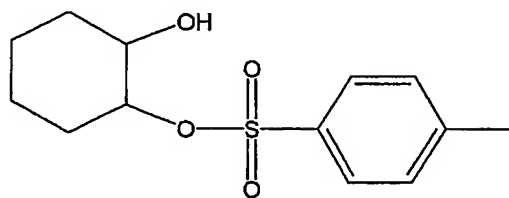
$l$ ,  $m$  and  $n$  are molar ratios:  $l$  ranging from 0.1 to 0.5,  $m$  ranging from 0.05 to 0.5,  $n$  ranging from 0.1 to 0.7, and  $l + m + n = 1$ ; and

15             $c$  is the degree of polymerization, ranging from 10 to 400.

5. The organic anti-reflective composition according to Claim 2, wherein said thermal acid generator is the compound represented by the following Chemical Formula

4:

Chemical Formula 4



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6. A patterning method comprising the steps of

(a) coating the organic anti-reflective composition according to Claim 1 on a part to be etched;

(b) crosslinking said organic anti-reflective composition by baking to form an organic anti-reflective film;

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(c) coating a photoresist on said organic anti-reflective film, and exposing and developing the same to form a photoresist pattern; and

(d) etching the organic anti-reflective film with said photoresist pattern as mask.

7. The patterning method according to Claim 6, wherein said baking of the step

(b) is carried out at 150 to 300 °C for 1 to 5 minutes.

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8. The patterning method according to Claim 6, wherein baking is further carried out before and/or after exposure of the step (c).

9. The patterning method according to Claim 8, wherein said baking is carried out

at 70 to 200 °C.

10. The patterning method according to Claim 6, wherein far UV such as F<sub>2</sub> laser (157 nm), ArF (193 nm), KrF (248 nm) and EUV (extremely ultraviolet); E-beam; X-ray; or ion beam is used as exposure light source in the step (c).

5           11. A semiconductor device prepared by any method according to Claims 6 to 10.